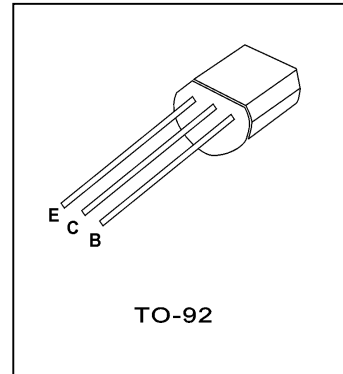


**EB SERIES TRANSISTORS****EB102**

- **FEATURES:** ■ HIGH VOLTAGE CAPABILITY    ■ HIGH SPEED SWITCHING    ■ WIDE SOA
- **APPLICATION:** ■ FLUORESCENT LAMP    ■ ELECTRONIC BALLAST

● **Absolute Maximum Ratings ( Tc=25°C )****TO-92**

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CBO}$	600	V
Collector-Emitter Voltage	$V_{CEO}$	400	V
Emitter- Base Voltage	$V_{EBO}$	9	V
Collector Current	$I_C$	0.6	A
Total Power Dissipation	$P_C$	8	W
Junction Temperature	$T_j$	150	°C
Storage Temperature	$T_{stg}$	-65-150	°C

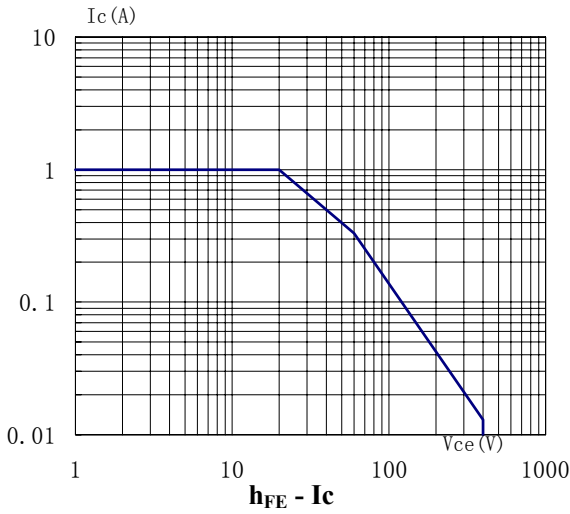
● **Electronic Characteristics ( Tc=25°C )**

CHARACTERISTICS	SYMBOL	TEST CONDITION	MIN	MAX	UNIT
Collector-Base Cutoff Current	$I_{CBO}$	$V_{CB}=600V$		100	$\mu A$
Collector-Emitter Cutoff Current	$I_{CEO}$	$V_{CE}=400V, I_B=0$		250	$\mu A$
Collector-Emitter Voltage	$V_{CEO}$	$I_C=10mA, I_B=0$	400		V
Emitter- Base Voltage	$V_{EBO}$	$I_E=1mA, I_C=0$	9		V
Collector-Emitter Saturation Voltage	$V_{ces}$	$I_C=0.1A, I_B=10mA$		0.5	V
		$I_C=0.4A, I_B=0.1A$		1.2	
		$I_C=0.8A, I_B=0.2A$		1.0	
Base-Emitter Saturation Voltage	$V_{bes}$	$I_C=0.2A, I_B=0.04A$		1.2	V
DC Current Gain	$h_{FE}$	$V_{CE}=5V, I_C=1mA$	8		
		$V_{CE}=5V, I_C=0.1A$	12	40	
		$V_{CE}=5V, I_C=50mA$	8		
Storage Time	$t_s$	$V_{CC}=250V,$		2.5	$\mu S$
Falling Time	$t_f$	$I_C=5I_B$ $I_{B1} = -I_{B2}=0.1A$		0.8	

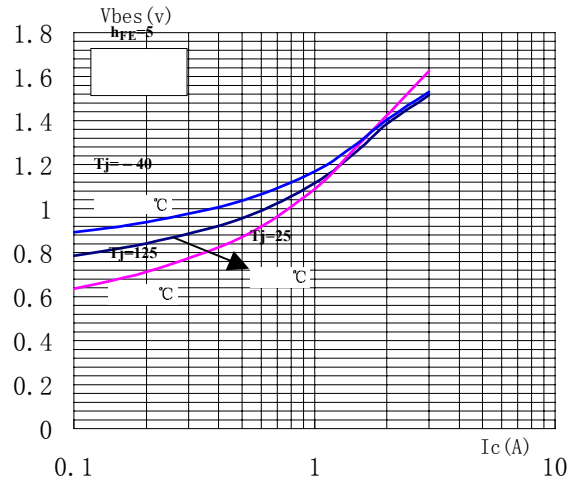
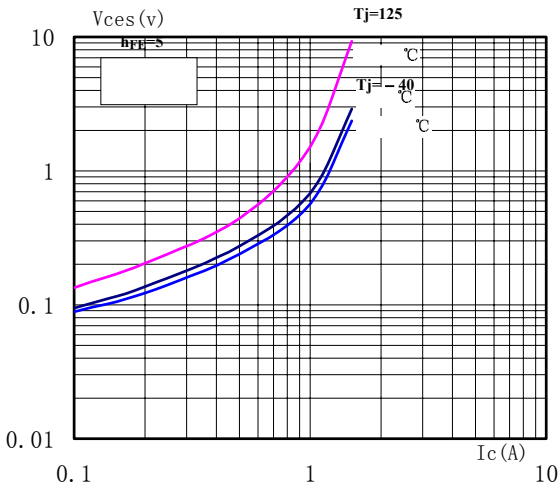
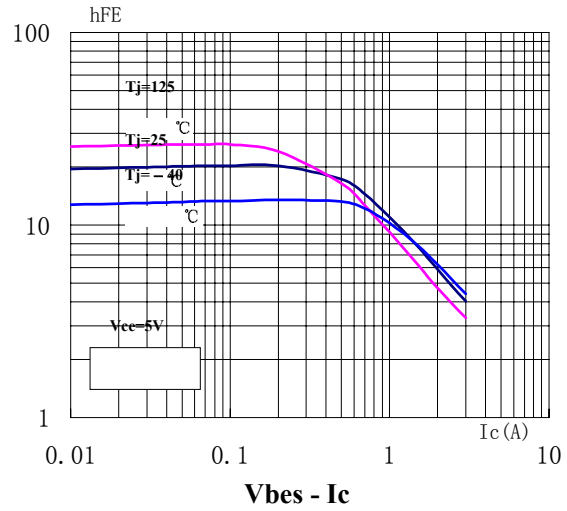
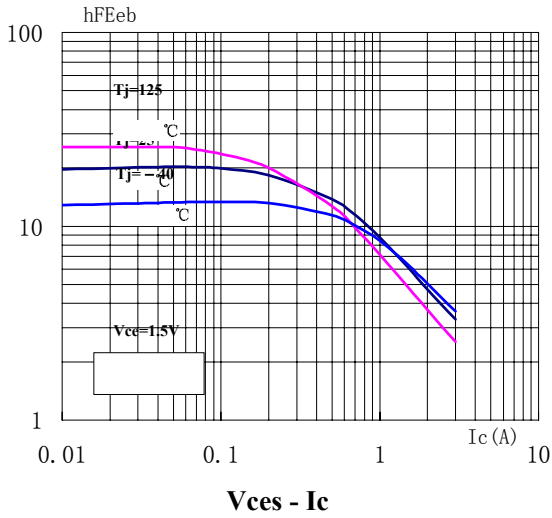
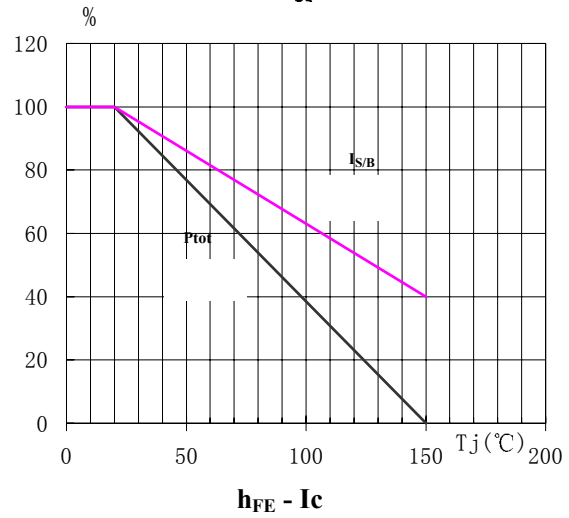
**EB SERIES TRANSISTORS**

**EB102**

**SOA (DC)**



**Pc Tj**



### TO-92 MECHANICAL DATA

UNIT: mm

SYMBOL	min	nom	max
A	4.3		5.3
b	0.3		
c	0.3		
$\phi D$	4.3		5.2
D			
d	1.0		1.7
E	3.2		4.2
e		2.54	
e1		1.27	
L	12.7		
L1			2.0

